# BONDING WIRE FOR SEMICONDUCTOR DEVICES

## ABSTRACT

A bonding wire for semiconductor devices and a method of manufacturing the same are disclosed. The bonding wire for semiconductor devices according to the present invention includes at least one selected from the group consisting of zinc (Zn), tin (Sn), and nickel (Ni) at 5 ppm to 10 wt%, and the remainder including silver (Ag) and other inevitable impurities.

Fig. 1